

Two-Dimensional Materials for Next-Generation Electronics: Innovation Opportunities and Industrial Applications

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Abstract

Two-dimensional (2D) materials have emerged as a significant class of advanced materials with the potential to reshape next-generation electronic and optoelectronic technologies. Their atomic-scale thickness, tunable electronic structures, high surface-to-volume ratios, mechanical flexibility and distinctive optical and electrical properties provide opportunities beyond the capabilities of conventional bulk semiconductors. This paper examines the technological potential of graphene, transition-metal dichalcogenides, hexagonal boron nitride, black phosphorus, MXenes and emerging van der Waals heterostructures for next-generation electronics. Particular attention is given to applications in field-effect transistors, flexible electronics, sensors, memory, neuromorphic computing, photodetectors, radio-frequency systems and energy-efficient integrated circuits. The paper analyses how properties such as high carrier mobility, strong light-matter interaction, tunable bandgaps and atomically thin structures can enable new device architectures. It also considers major barriers to industrial adoption, including large-area synthesis, defect control, contact resistance, environmental stability, device variability, integration with conventional semiconductor processes and manufacturing costs. A proposed innovation framework connects material discovery, scalable synthesis, device engineering, heterogeneous integration and industrial application. The paper argues that 2D materials are unlikely to replace silicon universally; instead, their greatest industrial impact is likely to emerge through complementary integration with established semiconductor technologies. Such hybrid architectures could enable highly miniaturised, flexible, energy-efficient and multifunctional electronic systems for artificial intelligence, sensing, communications, healthcare, automotive applications and advanced manufacturing.

Keywords: Two-Dimensional Materials, Graphene, Transition-Metal Dichalcogenides, MXenes, Nanoelectronics, Flexible Electronics, Semiconductor Technology, Van der Waals Heterostructures, Neuromorphic Computing, Advanced Materials.

1. Introduction

The semiconductor industry has achieved remarkable improvements in computing performance through decades of transistor scaling.

However, conventional semiconductor technologies increasingly face challenges involving:

- Power consumption.
- Heat dissipation.
- Short-channel effects.
- Interconnect limitations.
- Manufacturing complexity.
- Material scaling.

The search for alternative materials has therefore become an important component of next-generation electronics research.

Two-dimensional materials have attracted substantial attention because their thickness can approach the atomic scale while maintaining distinctive electrical, optical, mechanical and chemical characteristics.

Examples include:

- Graphene.
- Molybdenum disulfide (MoS_2).
- Tungsten disulfide (WS_2).
- Hexagonal boron nitride (h-BN).
- Black phosphorus.
- MXenes.

The transition can be conceptualised as:

Bulk Materials → Thin-Film Semiconductors → Atomically Thin Materials → Van der Waals Heterostructures

2. Fundamentals of Two-Dimensional Materials

2D materials are characterised by strong in-plane bonding and comparatively weak interactions between layers.

This structure enables individual atomic or molecular layers to be isolated or synthesised.

Their properties can differ significantly from their bulk counterparts.

Important characteristics include:

- Atomic-scale thickness.
- High surface area.
- Tunable electronic properties.
- Strong optical interactions.
- Mechanical flexibility.
- Interface engineering capability.

3. Major Classes of 2D Materials

The 2D-material landscape includes several important families.

Material	Major Characteristics	Potential Applications
Graphene	High conductivity, strength	Interconnects, sensors
MoS ₂	Semiconducting bandgap	Transistors, photodetectors
WS ₂	Strong optical properties	Optoelectronics
h-BN	Electrical insulation	Dielectrics, substrates
Black phosphorus	Tunable bandgap	Transistors, infrared devices
MXenes	High conductivity, surface chemistry	Sensors, energy devices

4. Graphene

Graphene consists of a single layer of carbon atoms arranged in a hexagonal lattice.

It exhibits:

- High electrical conductivity.
- High thermal conductivity.
- Exceptional mechanical strength.
- High carrier mobility.
- Optical transparency.

These characteristics make graphene attractive for:

- Conductive electrodes.
- Sensors.
- Flexible electronics.
- Interconnects.
- Transparent electronics.

5. The Bandgap Challenge of Graphene

Despite its excellent electrical properties, pristine graphene has no conventional bandgap.

This creates difficulties for digital transistor applications because efficient transistor switching requires the ability to strongly distinguish between on and off states.

Consequently, research has explored:

- Graphene nanoribbons.
- Chemical functionalisation.
- Structural modification.
- Heterostructure engineering.

6. Transition-Metal Dichalcogenides

Transition-metal dichalcogenides (TMDs) form an important class of semiconducting 2D materials.

Examples include:

- MoS₂.
- WS₂.
- MoSe₂.
- WSe₂.

Unlike graphene, many TMDs possess useful bandgaps.

This makes them attractive for transistor technologies.

7. MoS₂-Based Electronics

MoS₂ has become one of the most extensively studied 2D semiconductors.

Potential applications include:

- Field-effect transistors.
- Photodetectors.
- Sensors.
- Logic devices.
- Memory.

Its atomically thin structure may help control short-channel effects in highly scaled devices.

8. Hexagonal Boron Nitride

Hexagonal boron nitride is structurally similar to graphene but has very different electronic properties.

It is an electrical insulator with:

- High thermal stability.
- Strong dielectric behaviour.
- Atomically smooth surfaces.

It can serve as:

- A dielectric layer.
- A substrate.
- An encapsulation layer.

9. Black Phosphorus

Black phosphorus is a layered semiconductor with a tunable bandgap.

Its properties are particularly interesting for:

- Infrared photodetection.
- Field-effect transistors.
- Optical devices.

However, environmental instability remains a major challenge.

10. MXenes

MXenes are a family of two-dimensional transition-metal carbides and nitrides.

They offer:

- High electrical conductivity.
- Large surface area.
- Tunable surface chemistry.
- Good electromagnetic properties.

Potential applications include:

- Sensors.
- Electromagnetic shielding.
- Flexible electronics.
- Energy-storage devices.

11. Van der Waals Heterostructures

One of the most important opportunities involves stacking different 2D materials.

Because layers can be combined through van der Waals interactions, they do not necessarily need conventional lattice matching.

This enables architectures such as:

Graphene + h-BN + MoS₂ + WS₂

with each layer providing a different function.

12. Heterogeneous Material Engineering

The combination of different 2D materials allows researchers to engineer:

- Band alignment.
- Charge transfer.
- Optical response.
- Carrier transport.
- Interface properties.

This creates a modular approach to electronic-material design.

13. Field-Effect Transistors

2D materials are attractive for field-effect transistors because of their atomic thickness.

A simplified transistor structure contains:

Gate → Dielectric → 2D Semiconductor → Source/Drain

The extremely thin semiconductor channel can potentially improve electrostatic control.

14. Scaling Beyond Conventional Silicon

As transistor dimensions continue to decrease, electrostatic control becomes increasingly important.

2D semiconductors may offer advantages because the channel itself can be atomically thin.

Potential benefits include:

- Reduced short-channel effects.
- Strong gate control.
- Continued scaling potential.

15. Contact Resistance

One major challenge is the interface between metal contacts and 2D semiconductors.

High contact resistance can significantly reduce transistor performance.

Research is investigating:

- Novel contact metals.
- Edge contacts.
- Interface engineering.
- Doping strategies.

16. Flexible Electronics

The mechanical flexibility of many 2D materials makes them attractive for flexible devices.

Potential applications include:

- Wearable electronics.
- Flexible displays.
- Electronic skin.
- Smart textiles.
- Flexible sensors.

17. Stretchable Electronics

2D materials can potentially be incorporated into stretchable structures.

This could enable electronics that conform to:

- Human skin.
- Curved surfaces.
- Soft robotic systems.
- Biomedical interfaces.

18. Electronic Skin

Electronic skin requires sensors capable of detecting:

- Pressure.
- Temperature.
- Strain.

- Touch.

2D materials offer high surface sensitivity and can be integrated into flexible sensing platforms.

AI can subsequently interpret the resulting sensor data.

19. Biosensors

The high surface-to-volume ratio of 2D materials is particularly useful for biosensing. Surface functionalisation can allow interactions with:

- Proteins.
- DNA.
- Biomolecules.
- Chemical species.

This creates opportunities for highly sensitive diagnostic systems.

20. Gas and Chemical Sensors

Adsorption of molecules onto 2D surfaces can modify their electrical properties.

Consequently, 2D materials can be used to detect:

- Toxic gases.
- Environmental pollutants.
- Industrial chemicals.
- Volatile organic compounds.

21. Photodetectors

2D materials can exhibit strong interactions with light despite their small thickness.

This makes them attractive for photodetectors.

Potential applications include:

- Imaging.
- Optical communication.
- Environmental sensing.
- Infrared detection.

22. Optoelectronics

2D materials can combine electrical and optical functionality.

Potential devices include:

- Light emitters.
- Modulators.
- Photodetectors.
- Optical sensors.

Van der Waals heterostructures can further expand the available design space.

23. Memory Technologies

2D materials can potentially support emerging memory architectures.

Research areas include:

- Resistive memory.
- Ferroelectric memory.
- Phase-change structures.
- Memristive devices.

Their atomic-scale thickness can enable highly compact memory elements.

24. Neuromorphic Computing

Neuromorphic computing attempts to emulate aspects of biological information processing.

2D materials may provide tunable conductance states useful for artificial synapses.

A simplified concept is:

Input Signal → Conductance Change → Stored State → Output Response

This can support hardware implementations of learning algorithms.

25. AI Hardware

AI accelerators require:

- High computational density.
- Efficient memory access.
- Low energy consumption.

2D materials could contribute to:

- Transistors.
- Memory.
- Sensors.
- Photonic components.
- Neuromorphic devices.

26. Quantum Electronics

Some 2D materials exhibit unusual electronic phenomena that may be relevant to quantum technologies.

Potential research areas include:

- Excitons.
- Spin-dependent phenomena.
- Moiré systems.
- Quantum transport.

27. Moiré Engineering

When two 2D layers are stacked with a small rotational mismatch, a moiré pattern can emerge.

This can dramatically modify electronic properties.

Moiré structures have become an important research area for exploring:

- Correlated electronic states.
- Superconductivity.
- Quantum phenomena.

28. Thermal Management

The thermal properties of 2D materials may also be useful for electronics.

Graphene, for example, exhibits very high in-plane thermal conductivity.

Potential applications include:

- Heat spreaders.
- Thermal interface materials.
- Electronics cooling.

29. Electromagnetic Shielding

Conductive 2D materials can interact strongly with electromagnetic radiation.

Potential applications include:

- EMI shielding.
- Wireless electronics.
- Aerospace systems.
- Automotive electronics.

30. RF Electronics

High-frequency electronics require materials capable of operating at high frequencies.

Graphene and other 2D materials have been investigated for:

- RF transistors.
- Frequency mixers.
- High-speed detectors.

31. 6G and Advanced Communications

Future wireless networks may require:

- High-frequency operation.
- Compact antennas.
- Flexible components.
- Advanced sensing.

2D materials could contribute to:

- RF components.

- Antennas.
- Photodetectors.
- Terahertz devices.

32. Semiconductor Manufacturing Integration

Industrial adoption depends heavily on compatibility with existing semiconductor manufacturing.

Important considerations include:

- Wafer-scale synthesis.
- Process temperatures.
- Lithography compatibility.
- Contamination control.
- Yield.

33. Chemical Vapour Deposition

Chemical vapour deposition (CVD) is one of the leading approaches for producing large-area 2D materials.

Advantages include:

- Scalability.
- Potential wafer-scale production.
- Process compatibility.

However, achieving uniform quality remains challenging.

34. Exfoliation

Mechanical and liquid exfoliation can produce high-quality flakes.

However, these techniques are generally less attractive for high-volume industrial manufacturing because of:

- Limited scale.
- Variation in flake size.
- Placement challenges.

35. Defect Engineering

Defects can have both positive and negative effects.

They may:

- Reduce carrier mobility.
- Increase leakage.
- Alter optical properties.
- Create useful active sites.

Controlled defect engineering is therefore an important research direction.

36. Device Variability

Large-scale electronics require highly consistent devices.

2D-material devices may exhibit variability caused by:

- Material thickness.
- Defects.
- Grain boundaries.
- Contact interfaces.
- Environmental conditions.

Improving reproducibility is therefore essential.

37. Environmental Stability

Some 2D materials are sensitive to:

- Oxygen.
- Moisture.
- Light.

Encapsulation techniques can improve stability.

Materials such as h-BN can potentially act as protective layers.

38. Packaging

Advanced packaging is becoming increasingly important.

2D materials could be integrated through:

- Wafer-level transfer.
- Heterogeneous integration.
- 3D stacking.
- Chiplet architectures.

39. Industrial Applications

Major application sectors include:

Sector	Potential Application
Semiconductor	Transistors
AI	Neuromorphic hardware
Healthcare	Biosensors
Automotive	Sensors and electronics
Aerospace	EMI shielding
Telecommunications	RF and photonics
Energy	Electrodes and sensors

Sector	Potential Application
Manufacturing	Industrial monitoring

40. AI-Enabled Materials Discovery

Artificial intelligence can accelerate the discovery of new 2D materials.

Machine learning can predict:

- Stability.
- Electronic properties.
- Bandgaps.
- Defect behaviour.
- Interface characteristics.

This creates a feedback loop:

AI Prediction → Material Synthesis → Experimental Validation → New Data → Improved AI Model

41. Computational Materials Engineering

High-throughput computational approaches can screen large numbers of candidate materials.

AI models can reduce the time required to identify promising candidates for specific applications.

42. Digital Materials Design

The convergence of:

AI + Materials Science + High-Throughput Experimentation

can create accelerated materials-development pipelines.

This may shorten the path from discovery to industrial deployment.

43. Sustainability Considerations

The sustainability of 2D materials should be evaluated across their lifecycle.

Relevant issues include:

- Raw-material availability.
- Energy-intensive synthesis.
- Chemical usage.
- Waste generation.
- Recycling.

A material should not be considered sustainable simply because the final device is energy efficient.

44. Circular Manufacturing

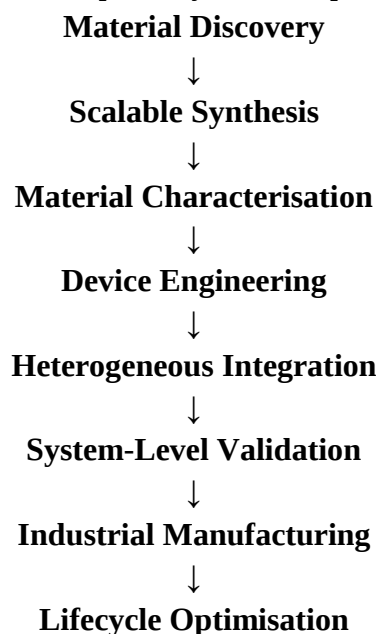
Future research should investigate:

- Material recovery.
- Device recycling.
- Low-energy synthesis.
- Reduced chemical waste.
- Reusable substrates.

This could support more sustainable electronics manufacturing.

45. Proposed Innovation Framework

A comprehensive industrial innovation pathway can be represented as:



46. Research Methodology

Future experimental studies can evaluate 2D-material devices through:

Independent Variables

- Material type.
- Number of layers.
- Synthesis method.
- Defect density.
- Contact architecture.

Dependent Variables

- Carrier mobility.
- On/off ratio.
- Contact resistance.

- Energy consumption.
- Device stability.
- Switching speed.

47. Evaluation Metrics

Metric	Significance
Carrier mobility	Charge transport
On/off ratio	Switching performance
Contact resistance	Interface quality
Switching speed	Computing performance
Energy/operation	Efficiency
Stability	Reliability
Yield	Manufacturing feasibility
Cost	Industrial viability

48. Research Questions

1. Which 2D materials offer the strongest opportunities for post-silicon electronics?
2. How can wafer-scale synthesis quality be improved?
3. What contact architectures minimise resistance?
4. How can 2D materials be integrated into existing CMOS processes?
5. Can AI accelerate discovery of commercially viable 2D materials?
6. Which 2D-material devices are closest to industrial deployment?
7. How can environmental stability be improved?
8. Can 2D materials enable scalable neuromorphic computing?
9. How can heterogeneous 2D-material stacks be manufactured economically?
10. What lifecycle strategies are required for sustainable 2D-material electronics?

49. Future Research Directions

Important areas include:

- Wafer-scale 2D synthesis.
- CMOS-compatible integration.
- 2D-material transistors.
- Photonic 2D devices.
- Neuromorphic computing.
- Flexible electronics.

- Electronic skin.
- AI-designed materials.
- Quantum materials.
- Sustainable 2D-material manufacturing.

50. Strategic Recommendations

Researchers and industry should:

1. Prioritise scalable synthesis.
2. Improve device reproducibility.
3. Develop CMOS-compatible integration processes.
4. Reduce contact resistance.
5. Improve environmental stability.
6. Develop standardised material-characterisation protocols.
7. Combine 2D materials with conventional semiconductors.
8. Use AI for accelerated material discovery.
9. Evaluate lifecycle sustainability.
10. Focus on application-specific commercial opportunities rather than universal silicon replacement.

51. Discussion

The industrial significance of 2D materials lies not simply in their unusual physical properties but in their potential integration into existing technology ecosystems.

Silicon remains extremely mature.

Consequently, replacing silicon entirely would face substantial economic and manufacturing barriers.

A more realistic strategy is complementary integration.

For example:

Silicon Logic + 2D Transistor + Graphene Interconnect + h-BN Dielectric + 2D Sensor could combine established semiconductor manufacturing with advanced material functionality.

52. From Material Innovation to System Innovation

The value of 2D materials will ultimately depend on their contribution at the system level.

A material with exceptional laboratory properties may have limited industrial value if it cannot achieve:

- Large-scale manufacturing.
- High yield.
- Long-term reliability.
- Competitive cost.

Therefore:

Material Performance $\neq$ Industrial Success

Industrial success requires:

Material Performance + Manufacturability + Reliability + Cost Competitiveness + Application Value

53. Conclusion

Two-dimensional materials represent one of the most promising material platforms for next-generation electronics.

Graphene, transition-metal dichalcogenides, hexagonal boron nitride, black phosphorus and MXenes offer distinctive combinations of electrical, optical, mechanical and chemical properties.

Their potential extends across:

- Nanoelectronics.
- Flexible electronics.
- Sensors.
- Photonics.
- AI hardware.
- Neuromorphic computing.
- RF systems.
- Healthcare.
- Advanced manufacturing.

Nevertheless, major barriers remain.

These include scalable synthesis, material uniformity, contact resistance, device variability, environmental stability, packaging and integration with established semiconductor processes.

The most realistic industrial pathway is therefore not to replace conventional semiconductor technology completely but to create hybrid material architectures in which 2D materials perform functions where their unique properties provide a measurable advantage.

The convergence of AI-driven materials discovery, scalable manufacturing and heterogeneous semiconductor integration could accelerate this transition.

The emerging paradigm can be summarised as:

Atomically Thin Materials + Advanced Device Engineering + AI-Assisted Discovery + Heterogeneous Integration $\rightarrow$ Next-Generation Electronic Systems.

With continued progress in manufacturing and system-level engineering, 2D materials could become an important technological foundation for more compact, flexible, energy-efficient and multifunctional electronic devices.

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